

German Gutierrez  
Application No.: 09/650,275  
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IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A die seal structure for a semiconductor die having a  
2 substrate comprising:  
3 an elongate region electrically isolated from the remainder of the substrate  
4 extending around a major portion of the periphery of the substrate and having a gap  
5 between ends of the elongate region along a minor portion of the periphery; and  
6 a conductive seal ring extending around the entire periphery of the die in  
7 direct contact with the die throughout said elongate region in direct contact with and said  
8 gap to provide a limited electrical connection between the ring and the substrate at said  
9 gap.

Please cancel claims 9-13. ~~14~~.

14. (Amended) A die seal structure for a semiconductor die having a  
2 substrate of a first conductivity type, comprising:  
3 an elongate well region of a second conductivity type opposite from the  
4 first conductivity type extending around a major portion of the periphery of the substrate  
5 and having a gap between the ends of the elongate region along a minor portion of the  
6 periphery; and  
7 a conductive seal ring extending around the entire periphery of the die in  
8 direct contact with the die throughout said elongate well region and in said gap to provide  
9 a limited electrical connection between the ring and the substrate of said first  
10 conductivity type at said gap.

18. (Amended) A semiconductor device comprising:  
2 a die including a substrate;

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